

Plastic Medium Power Silicon NPN Transistor

... designed for use in 5.0 to 10 Watt audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

- DC Current Gain hFE = 40 (Min) @ IC = 0.15 Adc
- BD179 is complementary with BD180

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter–Base Voltage	VEBO	5.0	Vdc
Collector Current	IC	3.0	Adc
Base Current	ΙΒ	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	30 240	Watts mw/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +150	°C

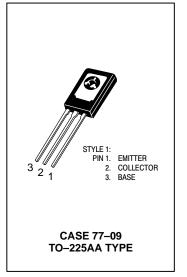
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	4.16	°C/W

BD179 BD179-10

3.0 AMPERES
POWER TRANSISTORS
NPN SILICON
80 VOLTS
30 WATTS

*ON Semiconductor Preferred Device



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage* (IC = 0.1 Adc, IB = 0)	V(BR)CEO	80	_	Vdc
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	ICBO	_	0.1	mAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, I _C = 0)	I _{EBO}	_	1.0	mAdc
DC Current Gain (I _C = 0.15 A, V _{CE} = 2.0 V) BD179–10 (I _C = 1.0 A, V _{CE} = 2.0 V) ALL	hFE	63 15	160 —	
Collector–Emitter Saturation Voltage* (IC = 1.0 Adc, IB = 0.1 Adc)	VCE(sat)	_	0.8	Vdc
Base–Emitter On Voltage* (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE} (on)	_	1.3	Vdc
Current–Gain – Bandwidth Product (I _C = 250 mAdc, V _{CE} = 10 Vdc, f = 1.0 MHz)	fT	3.0	_	MHz

1

^{*}Pulse Test: Pulse Width \leq 300 As, Duty Cycle \leq 2.0%.

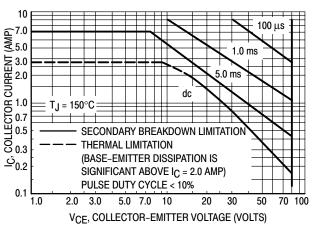


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power–temperature derating must be observed for both steady state and pulse power conditions.

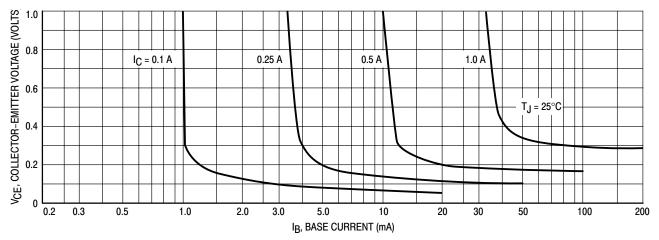


Figure 2. Collector Saturation Region

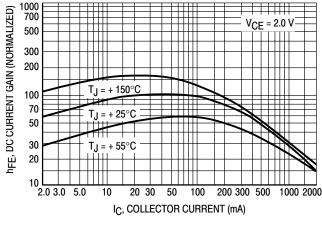


Figure 3. Current Gain

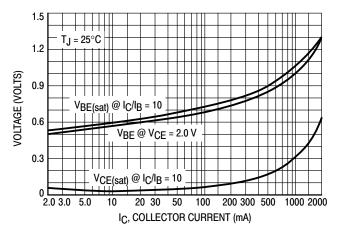


Figure 4. "On" Voltages

BD179 BD179-10

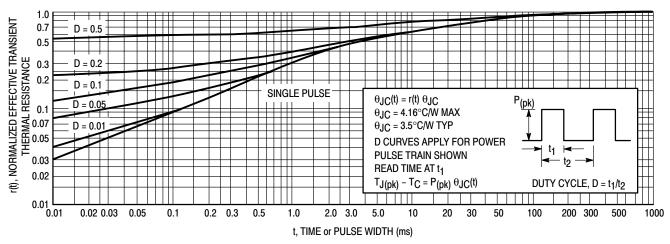
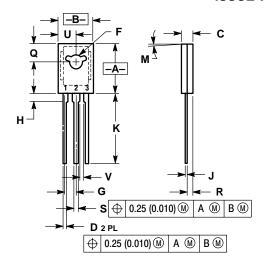


Figure 5. Thermal Response

PACKAGE DIMENSIONS

TO-225AA **CASE 77-09 ISSUE W**



- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.425	0.435	10.80	11.04
В	0.295	0.305	7.50	7.74
С	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094	BSC	2.39 BSC	
Н	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
٧	0.040		1.02	

STYLE 1:

PIN 1. EMITTER COLLECTOR

BASE

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